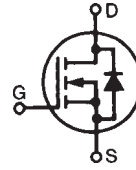


TrenchMV™ Power MOSFET

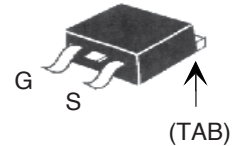
IXTA160N10T
IXTP160N10T

$$\begin{aligned} V_{DSS} &= 100 \text{ V} \\ I_{D25} &= 160 \text{ A} \\ R_{DS(on)} &\leq 7.0 \text{ m}\Omega \end{aligned}$$

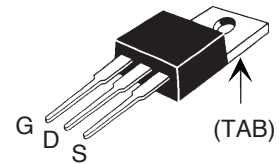
N-Channel Enhancement Mode
Avalanche Rated



TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$	100	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	160	A
I_{LRMS}	Lead Current Limit, RMS	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	430	A
I_{AR}	$T_C = 25^\circ\text{C}$	25	A
E_{AS}	$T_C = 25^\circ\text{C}$	500	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 175^\circ\text{C}$, $R_G = 5 \Omega$	3	V/ns
P_D	$T_C = 25^\circ\text{C}$	430	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-220	3	g
	TO-263	2.5	g

Features

- Ultra-low On Resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- 175 $^\circ\text{C}$ Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - 42V Power Bus
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary Switch for 24V and 48V Systems
- Distributed Power Architectures and VRMs
- Electronic Valve Train Systems
- High Current Switching Applications
- High Voltage Synchronous Rectifier

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.5		V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 25 \text{ A}$, Notes 1, 2	6.1	7.0	m Ω

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
(T _J = 25°C unless otherwise specified)				
g_{fs}	V _{DS} = 10 V; I _D = 60 A, Note 1	65	102	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		6600	pF
C_{oss}			880	pF
C_{rss}			135	pF
t_{d(on)}	Resistive Switching Times		33	ns
t_r	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 25 A		61	ns
t_{d(off)}	R _G = 5 Ω (External)		49	ns
t_f			42	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 25 A		132	nC
Q_{gs}			37	nC
Q_{gd}			40	nC
R_{thJC}	TO-220			0.35 °C/W
R_{thCH}			0.50	°C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		T _J = 25°C unless otherwise specified)		
		Min.	Typ.	Max.
I _S	V _{GS} = 0 V			160 A
I _{SM}	Pulse width limited by T _{JM}			430 A
V _{SD}	I _F = 25 A, V _{GS} = 0 V, Note 1			1.0 V
t _{rr}	I _F = 25 A, -di/dt = 100 A/μs V _R = 50 V, V _{GS} = 0 V		60	ns

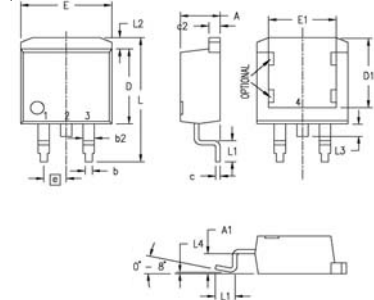
Notes: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$;
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5 mm or less from the package body.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

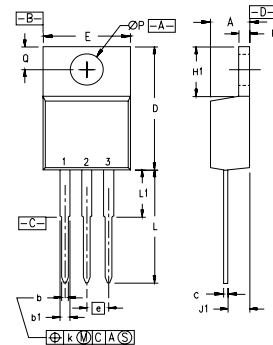
TO-263 (IXTA) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4, TAB - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

TO-220 (IXTP) Outline

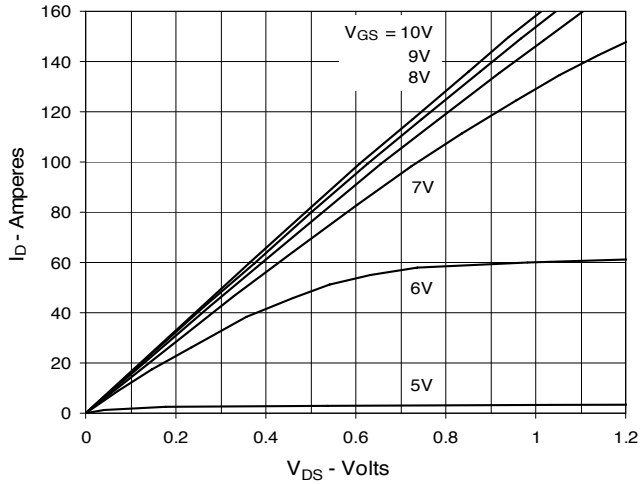


Pins: 1 - Gate 2 - Drain
3 - Source 4, TAB - Drain

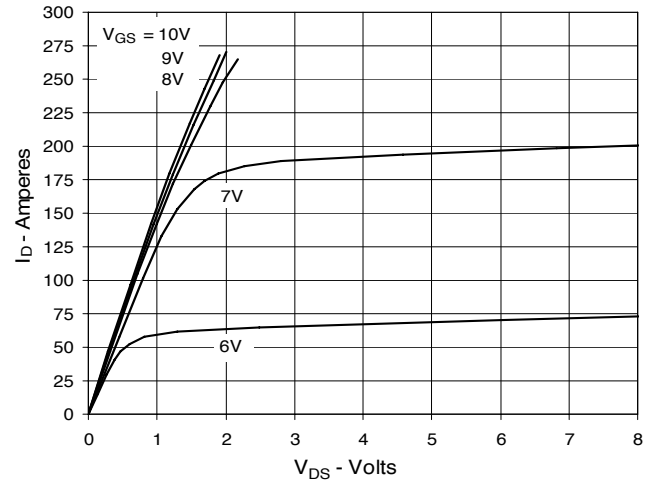
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100	BSC	2.54	BSC
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537

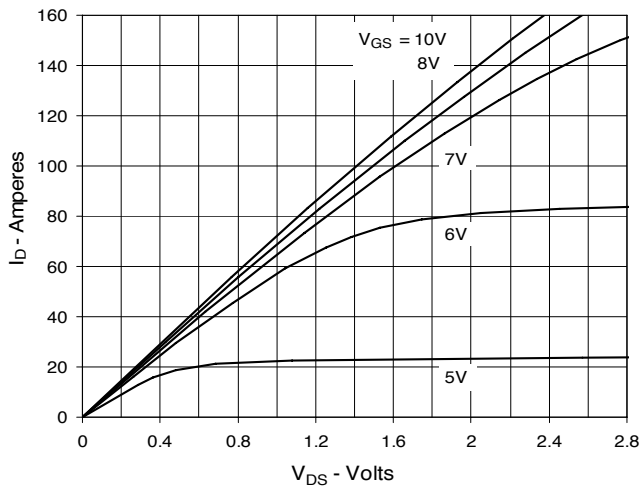
**Fig. 1. Output Characteristics
@ 25°C**



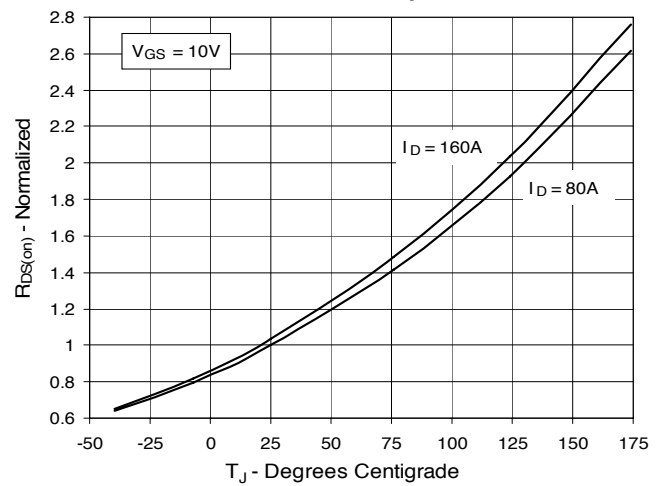
**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 3. Output Characteristics
@ 150°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 160A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 80A$ Value
vs. Drain Current**

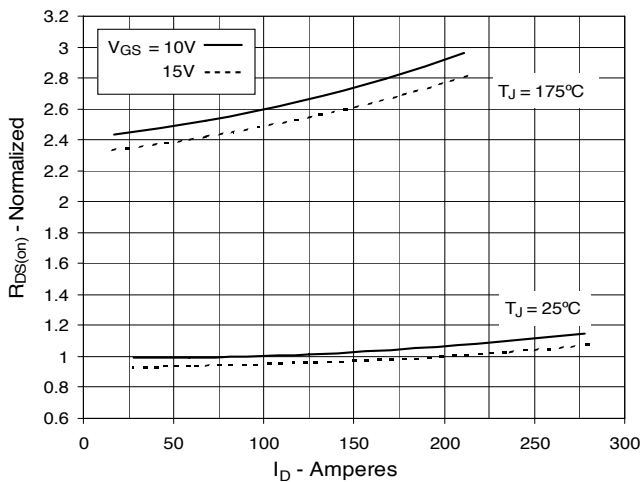


Fig. 6. Drain Current vs. Case Temperature

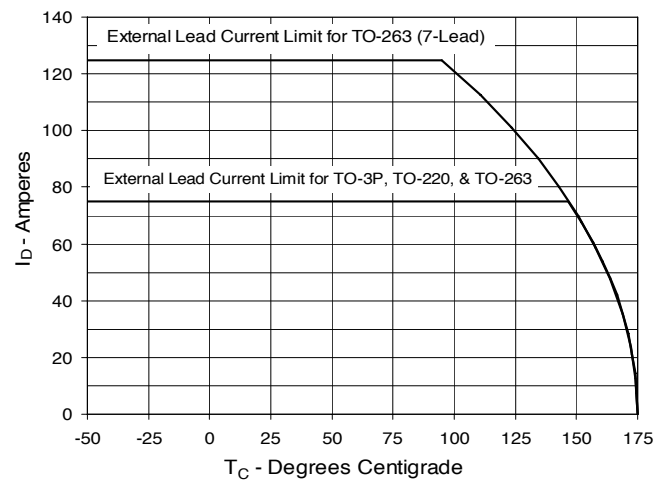


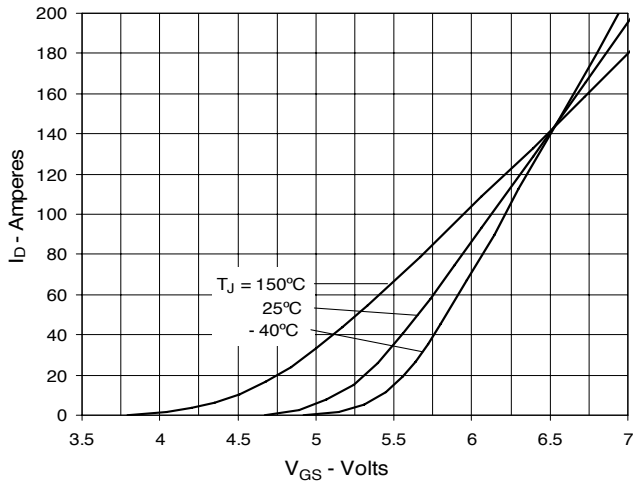
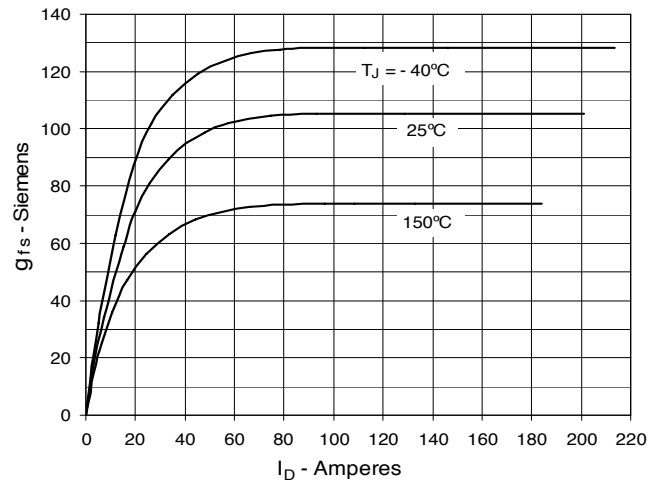
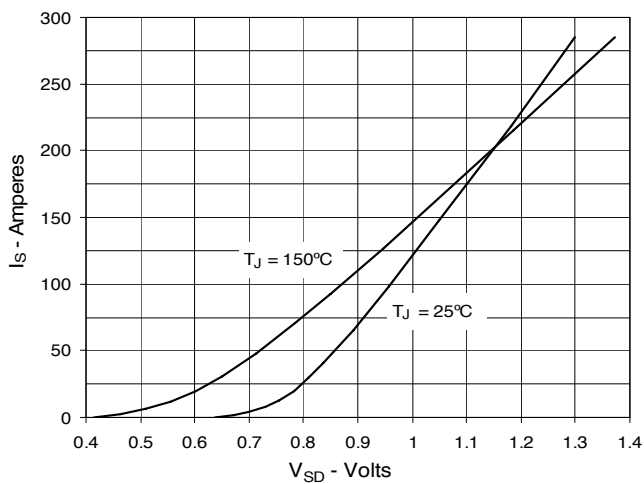
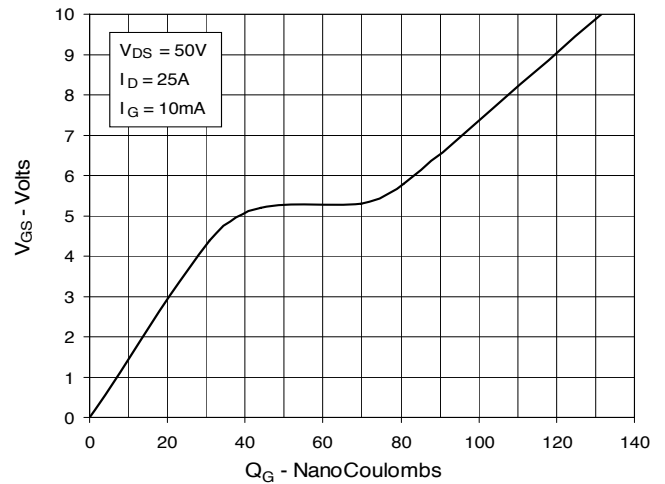
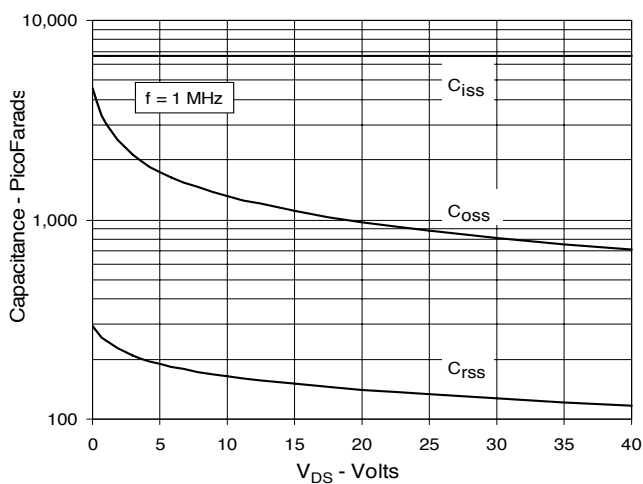
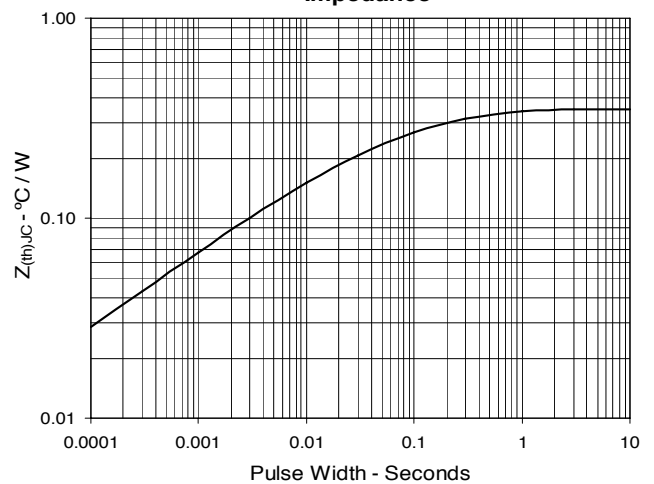
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance


Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature

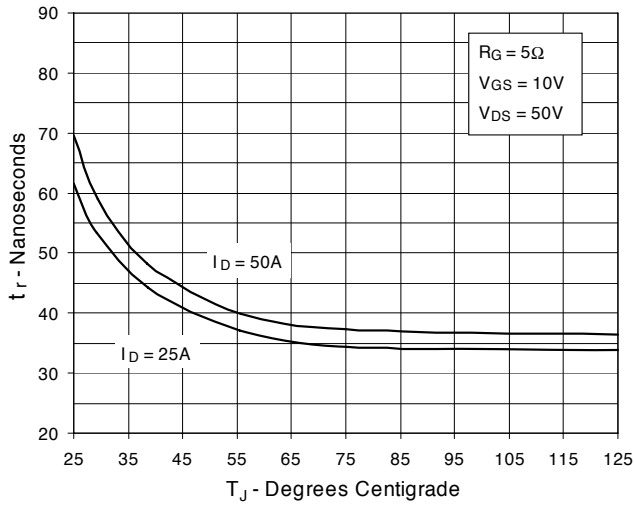


Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current

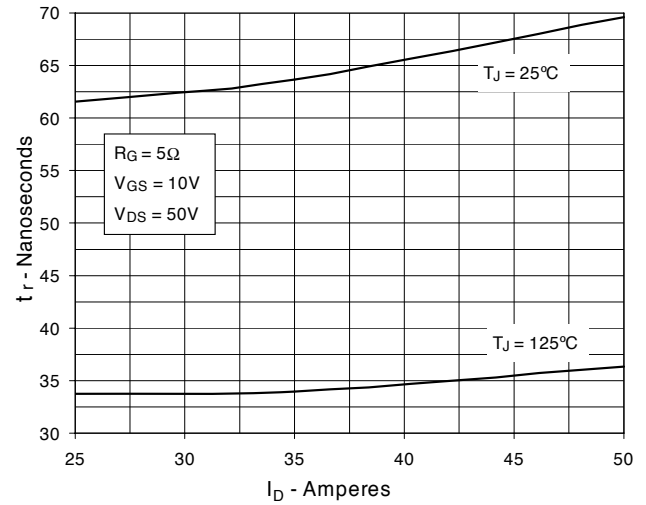


Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance

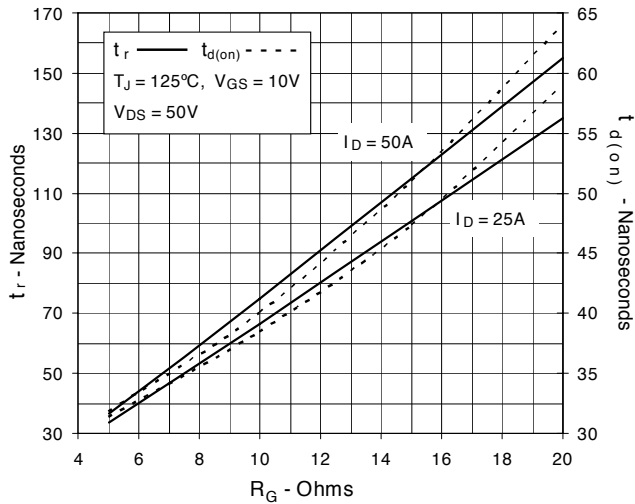


Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature

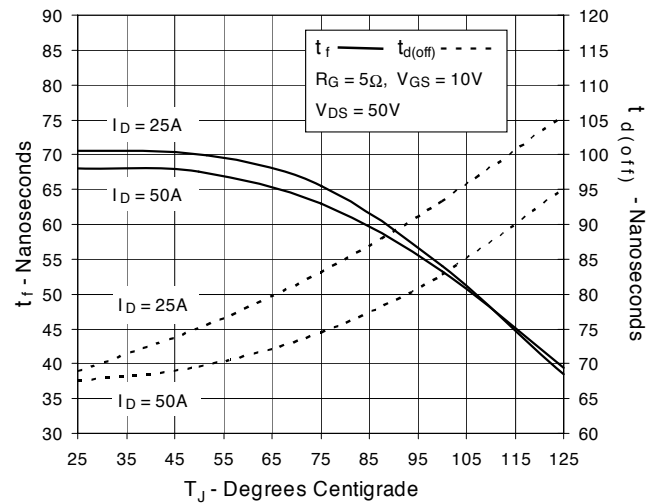


Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current

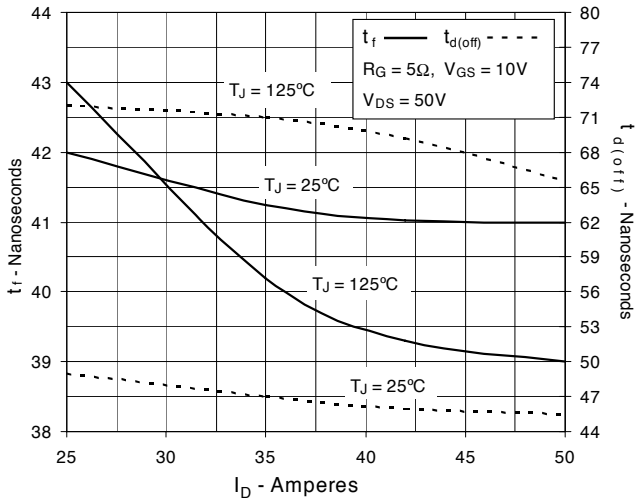


Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance

